

AN OPTICAL PROXIMITY CORRECTION METHOD

Abstract

An optical proximity correction (OPC) method first provides a pre-determined integrated circuit layout. The integrated circuit layout is then formed on a surface of a photo-mask, and a plurality of nonprintable dummy patterns are formed outside the integrated circuit layout on the surface of the photo-mask. The plurality of dummy patterns are used to reduce the difference in pattern density on the surface of the photo-mask so as to modify optical proximity effect, and the dummy patterns are not transferred to a photoresist layer formed on a semiconductor wafer during a photolithography process.